

10V Drive Nch MOSFET

R5005CNX

Structure

Silicon N-channel MOSFET

● Features

- 1) Low on-resistance.
- 2) Fast switching speed.
- 3) Gate-source voltage (Vgss) guaranteed to be ± 30 V.
- 4) Drive circuits can be simple.
- 5) Parallel use is easy.

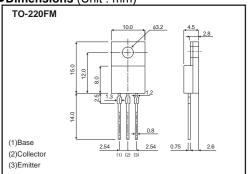
Applications

Switching

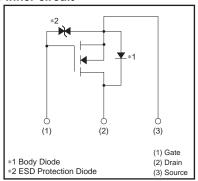
Packaging specifications

Туре	Package	Bulk
	Basic ordering unit (pieces)	500pcs

●Dimensions (Unit: mm)



•Inner circuit



●Absolute maximum ratings (Ta=25°C)

Parameter	Symbol		Limits	Unit	
Drain-source voltage	VDSS		500	V	
Gate-source voltage	Vgss		±30	V	
Droin ourrent	Continuous	ΙD	*3	±5	А
Drain current	Pulsed	IDP	*1	±20	А
Source current	Continuous	ls	*3	5	А
(Body Diode)	Pulsed	Isp	*1	20	А
Avalanche current	las	*2	2.5	А	
Avalanche energy	Eas	*2	1.6	mJ	
Total power dissipatio	Po		40	W	
Channel temperature	Tch		150	°C	
Range of storage tem	Tstg		-55 to +150	°C	

●Thermal resistance

Parameter	Symbol	Limits	Unit
Channel to case	Rth(ch-c)	3.13	°C/W

^{*1} Pw≤10μs, Duty cycle≤1% *2 L≒ 500μH, Vpp=50V, Rg=25Ω, Starting, Tch=25°C

^{*3} Limited only by maximum temperature allowed

●Electrical characteristics (Ta=25°C)

Parameter	Symbol	Min.	Тур.	Max.	Unit	Conditions
Gate-source leakage	lgss	_	_	±10	μΑ	Vgs=±30V, Vds=0V
Drain-source breakdown voltage	V(BR)DSS	500	_	_	V	ID=1mA, VGS=0V
Zero gate voltage drain current	IDSS	_	-	100	μΑ	Vps=500V, Vgs=0V
Gate threshold voltage	VGS(th)	2.5	_	4.5	V	VDS=10V, ID=1mA
Static drain-source on-state resistance	RDS(on)*	_	1.3	1.6	Ω	In=2.5A, Vgs=10V
Forward transfer admittance	Yfs *	1.5	_	_	S	ID=2.5A, VDS=10V
Input capacitance	Ciss	_	320	_	pF	Vps=25V
Output capacitance	Coss	_	180	_	pF	Vgs=0V
Reverse transfer capacitance	Crss	_	15	_	pF	f=1MHz
Turn-on delay time	td(on) *	-	20	_	ns	ID=2.5A, VDD≒250V
Rise time	tr *	_	25	_	ns	Vgs=10V
Turn-off delay time	td(off) *	_	40	_	ns	RL=100Ω
Fall time	t _f *	_	20	_	ns	R _G =10Ω
Total gate charge	Qg *	_	10.8	_	nC	V _{DD} ≒250V
Gate-source charge	Qgs *	_	3.2	-	nC	ID=5A Vgs=10V
Gate-drain charge	Qgd *	_	4.4	_	nC	$R_L=50\Omega$ / $R_G=10\Omega$

^{*} Pulsed

●Body diode characteristics (Source-drain) (Ta=25°C)

Parameter	Symbol	Min.	Тур.	Max.	Unit	Conditions
Forward voltage	Vsp*	_	-	1.5	V	I _S = 5A, V _{GS} =0V

^{*} Pulsed

R5005CNX Data Sheet

●Measurement circuit

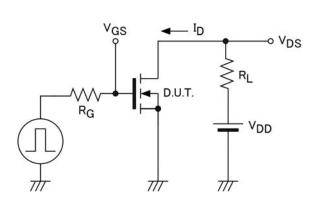


Fig.1 Switching time measurement circuit

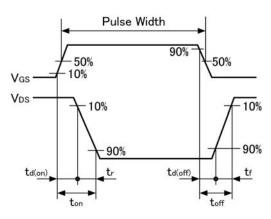


Fig.2 Switching waveforms

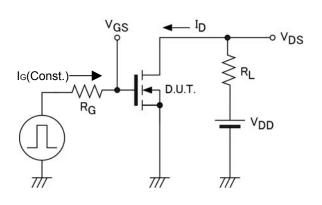


Fig.3 Gate charge measurement circuit

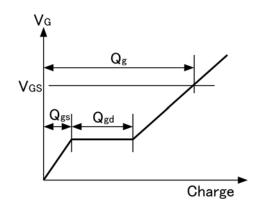


Fig.4 Gate charge waveform

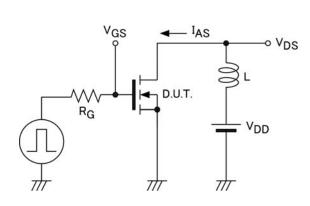


Fig.5 Avalanche measurement circuit

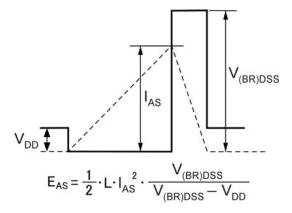


Fig.6 Avalanche waveform

Notes

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